

ABSTRACT

A semiconductor device includes: an active pattern protruding from a first active region; a first gate electrode on the active pattern; a second gate electrode on a second active region; a first gate insulating layer, including a first-first insulating layer, between the active pattern and the first gate electrode; and a second gate insulating layer, including a second-first insulating layer and a second-second insulating layer below the second-first insulating layer, between the second active region and the second gate electrode, wherein a thickness in a vertical direction of the first gate electrode that overlaps the active pattern in the vertical direction is equal to a thickness in the vertical direction of the second gate electrode that overlaps the second active region in the vertical direction, and an upper surface of the first gate electrode is formed at a same level as an upper surface of the second gate electrode.

FIG. 2